

ABSTRACT

1 A bonding structure with a buffer layer, and a method of forming the same are
2 provided. The bonding structure comprises a first substrate with metal pads thereon, a
3 protection layer covered on the surface of the substrate, a first adhesive metal layer
4 formed on the metal pads, a buffer layer coated on the protection layer and the metal pads,
5 a first metal layer covered on the buffer layer, and a second substrate with electrodes and
6 a bonding layer thereon. The first metal layer, the electrodes and the bonding layer are
7 bonded to form the bonding structure. Direct bonding can be performed through surface
8 activation or heat pressure. The method uses fewer steps and is more reliable. The
9 temperature required for bonding the structure is lower. The bonding density between the
10 contacted surfaces is increased to a fine pitch. The quality at the bonding points is
11 increased because fewer contaminations between the contacted surfaces are generated.